



## Multi-Channel LCD Gamma Correction Buffer

Check for Samples: BUF07703, BUF06703, BUF05703

#### **FEATURES**

Gamma Correction Channels: 6, 4

Integrated V<sub>COM</sub> Buffer

Excellent Output Current Drive:

- Gamma Channels: > 10mA

V<sub>COM</sub>: > 100mA typ

Large Capacitive Load Drive Capability

Rail-to-Rail Output

PowerPAD™ Package: BUF07703

Low-Power/Channel: < 250µA</li>

Wide Supply Range: 4.5V to 16V

Specified for –40°C to 85°C

High ESD Rating: 4kV HBM, 1.5kV CDM

#### **APPLICATIONS**

- LCD Flat Panel Displays
- LCD Television Displays

#### **DEVICE COMPARISON**

MODEL	GAMMA CHANNELS	V <sub>COM</sub> CHANNELS
BUF07703	6	1
BUF06703	6	0
BUF05703	4	1

#### DESCRIPTION

The BUFxx703 are a series of multi-channel buffers targeted towards gamma correction in high-resolution liquid crystal display (LCD) panels. The number of gamma correction channels required depends on a variety of factors and differs greatly from design to design. Therefore, various channel options are offered. For additional space and cost savings, a V<sub>COM</sub> channel with higher current drive capability is integrated in the BUF07703 and BUF05703.

A flow-through pinout has been adopted to allow simple printed circuit board (PCB) routing and maintain the cost-effectiveness of this solution. All inputs and outputs of the BUFxx703 incorporate internal ESD protection circuits that prevent functional failures at voltages up to 4kV HBM and 1.5kV CDM.

The various buffers within the BUFxx703 are carefully matched to the voltage I/O requirements for the gamma correction application. Each buffer is capable of driving heavy capacitive loads and offers fast load current switching. The  $V_{\text{COM}}$  channel has increased output drive of > 100mA and can handle even larger capacitive loads.

The BUF07703 is available in the HTSSOP PowerPAD™ package for dramatically increased power dissipation capability. The BUF06703 and BUF05703 are available in standard TSSOP-16 and TSSOP-14 packages.

#### **RELATED PRODUCTS**

DEVICE	GAMMA CHANNELS	V <sub>COM</sub> CHANNELS
BUF11702	10	1
BUF04701	4	_
TLV2374	4	_

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## PACKAGE INFORMATION(1)

PRODUCT	PACKAGE-LEAD	PACKAGE DESIGNATOR	PACKAGE MARKING
BUF07703	HTSSOP-20	PWP	BUF07703
BUF06703	TSSOP-16	PW	BUF06703
BUF05703	TSSOP-14	PW	BUF05703

<sup>(1)</sup> For the most current package and ordering information see the Package Option Addendum at the end of this document, or visit the device product folder at <a href="https://www.ti.com">www.ti.com</a>.

## **ABSOLUTE MAXIMUM RATINGS(1)**

Over operating free-air temperature range (unless otherwise noted).

	BUFxx703	UNIT
Supply, V <sub>DD</sub> <sup>(2)</sup>	16.5	16.5
Input Voltage Range, VI	$V_{DD}$	V
Continuous Total Power Dissipation	See Dissipation Ratings Table	
Operating Free-Air Temperature Range, T <sub>A</sub>	-40 to +85	°C
Maximum Junction Temperature, T <sub>J</sub>	+150	°C
Storage Temperature Range, T <sub>STG</sub>	−65 to +150	°C

<sup>(1)</sup> Stresses above these ratings may cause permanent damage. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### **DISSIPATION RATINGS**

PACKAGE TYPE	PACKAGE DESIGNATOR	θ <sub>JC</sub> (°C/W)	θ <sub>JA</sub>	T <sub>A</sub> ≤ +25°C POWER RATING
TSSOP-20 PowerPAD	PWP (20)	1.40 <sup>(1)</sup>	32.63 <sup>(1)</sup>	3.83W <sup>(1)</sup>
TSSOP-16	PW (16)	_	108	1.15W
TSSOP-14	PW (14)	_	112	1.11W

<sup>(1)</sup> Thermal specifications assume 2oz. trace and copper pad with solder.

## RECOMMENDED OPERATING CONDITIONS

Over operating free-air temperature range (unless otherwise noted).

		MIN	NOM MAX	UNIT
Supply Voltage, V <sub>DD</sub>		4.5	16	V
Operating Free-Air Temperature, T <sub>A</sub>		-40	+85	°C
harden Transcritor	TSSOP-20 PowerPAD		+125	°C
Junction Temperature	TSSOP-16, 14		+150	°C

2

<sup>(2)</sup> All voltage values are with respect to GND.



## **ELECTRICAL CHARACTERISTICS**

					BUF07703,	BUF07703, BUF06703, BUF05703			
PARAMETER		CONDITIONS	T <sub>A</sub> <sup>(1)</sup>	MIN	TYP	MAX	UNIT		
			V V /0 D 500	+25°C		1.5	1.2	mV	
$V_{IO}$	Input offset vo	itage	$V_I = V_{DD}/2$ , $R_S = 50\Omega$	Full range			15	mV	
	land thing are		V V /0	+25°C		1		pА	
I <sub>IB</sub>	Input bias curr	ent	$V_I = V_{DD}/2$	Full range		200		pA	
le.	Supply voltage	rejection ratio	V <sub>DD</sub> = 4.5V to 16V	+25°C	62	80		dB	
k <sub>SVR</sub>	$(\Delta V_{DD}/\Delta V_{IO})$		V <sub>DD</sub> = 4.5V to 16V	Full range	60			dB	
	Buffer gain		$V_I = 5V$	+25°C		0.9995		V/V	
BW_3dB	3dB	Gamma buffers	$C_L = 100pF, R_L = 2k\Omega$	+25°C		0.8		MHz	
DW_3ub	bandwidth	V <sub>COM</sub> buffer	$C_L = 100pF, R_L = 2k\Omega$	+25°C		0.7		MHz	
CD	Gamma b		$C_L = 100 pF, R_L = 2k\Omega$ $V_{IN} = 2V \text{ to } 8V$	+25°C		1		V/μs	
SR	Slew rate	Siew rate	V <sub>COM</sub> buffer	$C_L = 100 pF, R_L = 2k\Omega$ $V_{IN} = 2V \text{ to } 8V$	+25°C		0.7		V/μs
	Transient load	regulation	$I_O = 0 \text{ to } \pm 5\text{mA}, \ V_O = 5\text{V}$ $C_L = 100\text{pF}, \ t_T = 0.1\mu\text{s}$	+25°C		900		mV	
	Transient load	response	See Figure 3	+25°C		160		mV	
t <sub>S, (I-sink)</sub>	Settling time-o	current	$I_O = 0$ to $-5$ mA, $V_O = 5$ V $C_L = 100$ pF, $R_L = 2$ k $\Omega$	Full range		1		μS	
t <sub>S, (I-src)</sub>	Settling time-o	current	$I_O = 0 \text{ to } +5\text{mA}, \ V_O = 5\text{V}$ $C_L = 100\text{pF}, \ R_L = 2\text{k}\Omega$	Full range		2		μs	
		0	V <sub>I</sub> = 4.5V to 5.5V, 0.1%	+25°C		6		μS	
	Settling time-	Gamma buffers	V <sub>I</sub> = 5.5V to 4.5V, 0.1%	+25°C		4.6		μS	
t <sub>S</sub>	voltage	\/ b#*a=	V <sub>I</sub> = 4.5V to 5.5V, 0.1%	+25°C		5.8		μS	
		V <sub>COM</sub> buffer	V <sub>I</sub> = 5.5V to 4.5V, 0.1%	+25°C		5.6		μS	
\ /	Noise velts ==	Gamma buffers	$V_I = 5V$ , $f = 1kHz$	+25°C		45		nV/√ <del>Hz</del>	
V <sub>n</sub>	Noise voltage	V <sub>COM</sub> buffer	$V_I = 5V$ , $f = 1kHz$	+25°C		40		nV/√ <del>Hz</del>	
	Crosstalk		$V_{IPP} = 6V, f = 1kHz$	+25°C		85		dB	

<sup>(1)</sup> Full range is -40°C to +85°C.



## **ELECTRICAL CHARACTERISTICS: BUF07703**

					BUF07703			
PARAMETER		PARAMETER		T <sub>A</sub> <sup>(1)</sup>	MIN	TYP	MAX	UNIT
	Committee and a second	All	$V_{O} = V_{DD}/2, V_{I} = V_{DD}/2,$	+25°C		1.7	2	mA
DD Supply current		All	$V_{DD} = 10V$	Full range			3	mA
		Buffers 1-3		+25°C	1		$V_{DD}$	V
	Common-mode input range	Buffers 4-6		+25°C	0		V <sub>DD</sub> – 1	V
	pat range	V <sub>COM</sub> buffer		+25°C	1		$V_{DD}$	V
		V <sub>COM</sub> buffer sinking	$V_{DD} = 10V, I_{O} = 1 \text{mA to } 30 \text{mA}$	+25°C		1		mV/mA
	Load regulation	V <sub>COM</sub> buffer sourcing	$V_{DD} = 10V$ , $I_{O} = -1$ mA to $-30$ mA	+25°C		1		mV/mA
	Load regulation	Buffers 1–6 sinking	$V_{DD} = 10V, I_{O} = 1 \text{mA to } 10 \text{mA}$	+25°C		0.85		mV/mA
		Buffers 1–6 sourcing	$V_{DD} = 10V$ , $I_{O} = -1$ mA to $-10$ mA	+25°C		0.85		mV/mA
V <sub>OSH1</sub>	High-level saturated	Buffer 1	$V_{DD} = 16V, V_{IO} = -5mA, V_{I} = 16V$	+25°C	15.85	15.9		V
OSH1	output voltage	Duller 1	V <sub>I</sub> = 16V	Full range	15.8			V
osl6	Low-level saturated	Buffer 6	$V_{DD} = 16V, V_{IO} = 5mA, V_{I} = 0V$	+25°C		0.1	0.15	V
OSL6	output voltage	Bullet 0	$V_I = 0V$	Full range			0.2	V
/ <sub>OH1</sub>	High-level output		$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	9.75	9.8		V
OH1	voltage	Bullet 1	$V_1 = 9.8V$	Full range	9.7			V
/ <sub>OH2/3</sub>	High-level output	Buffer 2/3	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	9.45	9.5		V
OH2/3	voltage	Duller 2/3	$V_1 = 9.5V$	Full range	9.4			V
/ <sub>OH4/5</sub>	High-level output	Buffer 4/5	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	7.95	8		V
VH4/5	voltage	Ballot 1/0	V <sub>I</sub> = 8V	Full range	7.9			V
√ <sub>OH6</sub>	High-level output	Buffer 6	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	7.95	8		V
OH6	voltage	Ballot	V <sub>I</sub> = 8V	Full range	7.9			V
/онсом	High-level output	V <sub>COM</sub> buffer	$V_{DD} = 10V, V_{IO} = -30mA,$	+25°C	7.95	8		V
OHCOM	voltage	COM Sano.	V <sub>I</sub> = 8V	Full range	7.9			V
/ <sub>OL1</sub>	Low-level output	Buffer 1	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 2V$	+25°C		2	2.05	V
OLI	voltage	24	7 <sub>00</sub> 1917, 10 1911, 17 21	Full range			2.1	V
/ <sub>OL2/3</sub>	Low-level output	Buffer 2/3	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 2V$	+25°C		2	2.05	V
OL2/3	voltage	Ballot 270	VDD = 10 V, 10 = 1011111, V1 = 2 V	Full range			2.1	V
101.45	Low-level output	Buffer 4/5	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 0.5V$	+25°C		0.5	0.55	V
V <sub>OL4/5</sub> voltage		Dullet 4/5 $V_{DD} = 10V$ , $I_{O} = 10MA$ , $V_{I} =$	ν <sub>DD</sub> = 10ν, 10 = 10πν, ν  = 0.5ν	Full range			0.6	V
√ <sub>OL6</sub>	Low-level output	Buffer 6	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 0.2V$	+25°C		0.2	0.25	V
OL6	voltage	Dalloi 0	ν <sub>υυ</sub> = 10ν, ιο = 10πν, ν  = 0.2ν	Full range			0.3	V
V <sub>OLCOM</sub>	Low-level output	V <sub>COM</sub> buffer	$V_{DD} = 10V, I_{O} = 30mA, V_{I} = 2V$	+25°C		2	2.05	V
• OLCOM	voltage	A COW panel	VDD - 10V, 10 = 30111A, VI = 2V				2.1	V

<sup>(1)</sup> Full range is -40°C to +85°C.



## **ELECTRICAL CHARACTERISTICS: BUF06703**

						BUF06703		
PARAMETER		₹	CONDITIONS	T <sub>A</sub> <sup>(1)</sup>	MIN	TYP	MAX	UNIT
0 1		All	$V_{O} = V_{DD}/2, V_{I} = V_{DD}/2,$	+25°C		1.7	2	mA
DD	Supply current	All	$V_{DD} = 10V$	Full range			3	mA
	Common-mode	Buffers 1-3		+25°C	1		$V_{DD}$	V
	input range	Buffers 4-6		+25°C	0		V <sub>DD</sub> – 1	V
		Buffers 1–6 sinking	V <sub>DD</sub> = 10V, I <sub>O</sub> = 1mA to 10mA	+25°C		0.85		mV/mA
	Load regulation	Buffers 1–6 sourcing	$V_{DD} = 10V, I_{O} = -1mA \text{ to } -10mA$	+25°C		0.85		mV/mA
.,	High-level saturated	Buffer 1	V <sub>DD</sub> = 16V, V <sub>IO</sub> = −5mA,	+25°C	15.85	15.9		V
V <sub>OSH1</sub>	output voltage	Buffer 1	V <sub>I</sub> = 16V	Full range	15.8			V
.,	Low-level saturated	Buffer 6	V <sub>DD</sub> = 16V, V <sub>IO</sub> = 5mA,	+25°C		0.1	0.15	V
V <sub>OSL6</sub>	output voltage	Buffer 6	$V_1 = 0V$	Full range			0.2	V
	High-level output		$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	9.75	9.8		V
V <sub>OH1</sub>	voltage Buffer			Full range	9.7			V
.,	High-level output	Buffer 2/3	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	9.45	9.5		V
V <sub>OH2/3</sub>	voltage	Bullet 2/3	V <sub>I</sub> = 9.5V	Full range	9.4			V
.,	High-level output	Buffer 4/5	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	7.95	8		V
V <sub>OH4/5</sub>	voltage	Bullet 4/5	V <sub>I</sub> = 8V	Full range	7.9			V
.,	High-level output	Duffer C	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	7.95	8		V
V <sub>OH6</sub>	voltage	Buffer 6	$V_I = 8V$	Full range	7.9			V
,	Low-level output	Buffer 1	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 2V$	+25°C		2	2.05	V
V <sub>OL1</sub>	voltage	Buffer 1	$V_{DD} = 10V$ , $I_0 = 10$ mA, $V_1 = 2V$	Full range			2.1	V
.,	Low-level output	Buffer 2/3	V <sub>DD</sub> = 10V, I <sub>O</sub> = 10mA, V <sub>I</sub> = 2V	+25°C		2	2.05	V
V <sub>OL2/3</sub>	voltage	Dullel 2/3	$v_{DD} = 10V$ , $i_0 = 10HA$ , $V_1 = 2V$	Full range			2.1	V
Low-level output		Buffer 4/5	V = 10V L = 10mA V = 0.5V	+25°C		0.5	0.55	V
V <sub>OL4/5</sub>	voltage	Dullel 4/5	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 0.5V$	Full range			0.6	V
.,	Low-level output	Buffor 6	V = 10V L = 10mA V = 0.2V	+25°C		0.2	0.25	V
V <sub>OL6</sub>	voltage	Buffer 6 $V_{DD} = 10V, I_{O} = 10mA, V_{I} = 0.2V$		Full range			0.3	V

<sup>(1)</sup> Full range is -40°C to +85°C.



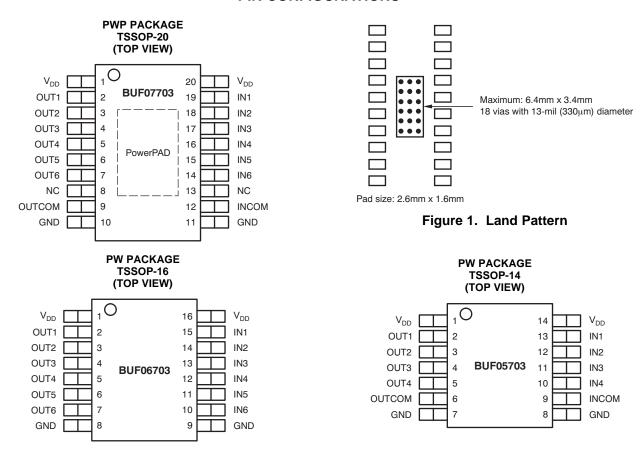
## **ELECTRICAL CHARACTERISTICS: BUF05703**

					BUF05703			
	PARAMETER	₹	CONDITIONS	T <sub>A</sub> <sup>(1)</sup>	MIN	TYP	MAX	UNIT
	Supply current All		$V_{O} = V_{DD}/2, V_{I} = V_{DD}/2,$	+25°C		1.7	2	mA
I <sub>DD</sub> Supply current		All	V <sub>DD</sub> = 10V	Full range			3	mA
		Buffers 1-2		+25°C	1		$V_{DD}$	V
	Common-mode input range	Buffers 3-4		+25°C	0		V <sub>DD</sub> – 1	V
		V <sub>COM</sub> buffer		+25°C	1		$V_{DD}$	V
		V <sub>COM</sub> buffer sinking	$V_{DD} = 10V, I_{O} = 1mA \text{ to } 30mA$	+25°C		1		mV/mA
	Load regulation	V <sub>COM</sub> buffer sourcing	$V_{DD} = 10V$ , $I_{O} = -1$ mA to $-30$ mA	+25°C		1		mV/mA
	Load regulation	Buffers 1–4 sinking	V <sub>DD</sub> = 10V, I <sub>O</sub> = 1mA to 10mA	+25°C		0.85		mV/mA
		Buffers 1–4 sourcing	$V_{DD} = 10V$ , $I_{O} = -1$ mA to $-10$ mA	+25°C		0.85		mV/mA
V <sub>OSH1</sub>	High-level saturated	Buffer 1	$V_{DD} = 16V, V_{IO} = -5mA, V_{I} = 16V$	+25°C	15.85	15.9		V
VOSH1	output voltage	Duller 1	V <sub>I</sub> = 16V	Full range	15.8			V
V <sub>OSL4</sub>	Low-level saturated	Buffer 4	$V_{DD} = 16V, V_{IO} = 5mA,$	+25°C		0.1	0.15	V
VOSL4	output voltage	Bullet 4	$V_I = 0V$	Full range			0.2	V
V <sub>OH1</sub>	High-level output	Buffer 1	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	9.75	9.8		V
VOH1	voltage	Duller 1	V <sub>I</sub> = 9.8V	Full range	9.7			V
$V_{OH2}$	High-level output	Buffer 2	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	9.45	9.5		V
V OH2	voltage	Buildi 2	V <sub>I</sub> = 9.5V	Full range	9.4			V
$V_{OH3}$	High-level output	Buffer 3	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	7.95	8		V
VOH3	voltage	Barror o	V <sub>I</sub> = 8V	Full range	7.9			V
$V_{OH4}$	High-level output	Buffer 4	$V_{DD} = 10V, V_{IO} = -10mA,$	+25°C	7.95	8		V
V OH4	voltage	Barror	V <sub>I</sub> = 8V	Full range	7.9			V
V <sub>OHCOM</sub>	High-level output	V <sub>COM</sub> buffer	$V_{DD} = 10V, V_{IO} = -30mA,$	+25°C	7.95	8		V
• ОНСОМ	voltage	V COM Bullot	V <sub>I</sub> = 8V	Full range	7.9			V
$V_{OL1}$	Low-level output	Buffer 1	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 2V$	+25°C		2	2.05	V
VOL1	voltage	Barror	VDD = 10 V, 10 = 101111V, V1 = 2 V	Full range			2.1	V
$V_{OL2}$	Low-level output	Buffer 2	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 2V$	+25°C		2	2.05	V
VOL2	voltage	Buildi 2	VDB = 10V, 10 = 1011/1, V1 = 2V	Full range			2.1	V
$V_{OL3}$	Low-level output	Buffer 3	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 0.5V$	+25°C		0.5	0.55	V
*OL3	voltage	241101 0	1011/1, 1 - 0.31	Full range			0.6	V
$V_{OL4}$	Low-level output	Buffer 4	$V_{DD} = 10V, I_{O} = 10mA, V_{I} = 0.2V$	+25°C		0.2	0.25	V
* OL4	voltage	Dallot 4	ν <sub>DD</sub> = 10 ν, 10 = 1011/λ, ν  = 0.2 ν	Full range			0.3	V
$V_{OLCOM}$	Low-level output	V <sub>COM</sub> buffer	$V_{DD} = 10V, I_{O} = 30mA, V_{I} = 2V$	+25°C		2	2.05	V
OLCOM	voltage	V <sub>DD</sub> = 10V, 10 = 3011A, V <sub>1</sub> = 2V		Full range			2.1	V

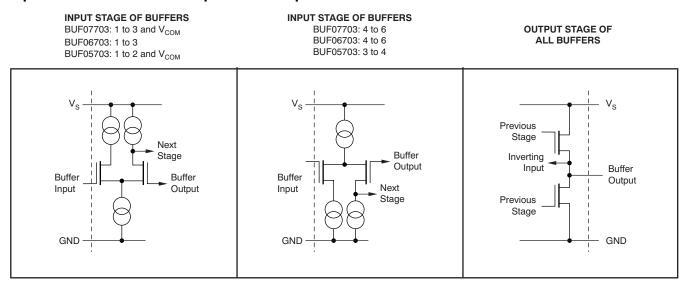
<sup>(1)</sup> Full range is -40°C to +85°C.



#### PIN CONFIGURATIONS



## **Equivalent Schematics of Inputs and Outputs**





## PARAMETER MEASUREMENT INFORMATION

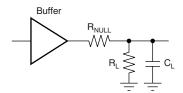
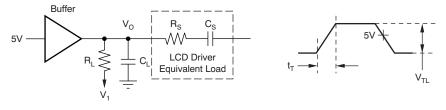


Figure 2. Bandwidth and Phase Shift Test Circuit



Test		V <sub>1</sub>	V <sub>TL</sub>	t <sub>T</sub>	cs	R <sub>s</sub>	CL	$R_L$
Source	Gamma Channels	0V	2V	0.1μs	100pF	100Ω	100pF	1kΩ
Sink	Gamma Channels	10V	2V	0.1μs	100pF	100Ω	100pF	1kΩ

Figure 3. Transient Load Response Test Circuit

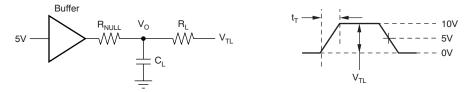


Figure 4. Transient Load Regulation Test Circuit



## TYPICAL CHARACTERISTICS

At  $V_{DD} = 10V$ , unless otherwise noted.

#### DC CURVES



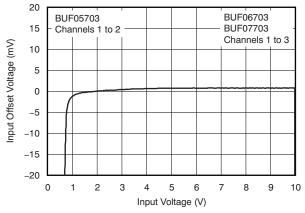


Figure 5.

#### **INPUT OFFSET VOLTAGE vs INPUT VOLTAGE**

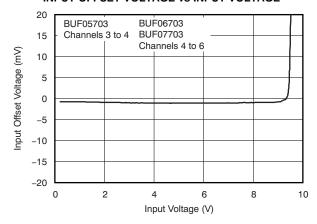


Figure 6.

#### **INPUT OFFSET VOLTAGE vs INPUT VOLTAGE**

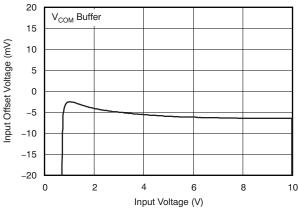


Figure 7.

#### INPUT BIAS CURRENT vs FREE-AIR TEMPERATURE

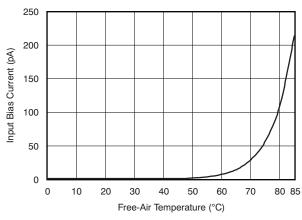


Figure 8.

#### HIGH-LEVEL OUTPUT VOLTAGE vs HIGH-LEVEL OUTPUT CURRENT

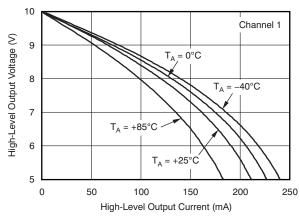


Figure 9.

#### HIGH-LEVEL OUTPUT VOLTAGE vs HIGH-LEVEL OUTPUT CURRENT

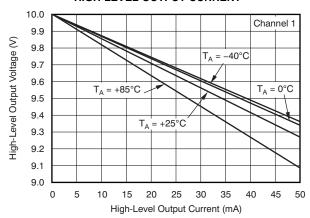


Figure 10.



At  $V_{DD}$  = 10V, unless otherwise noted.

## HIGH-LEVEL OUTPUT VOLTAGE vs HIGH-LEVEL OUTPUT CURRENT

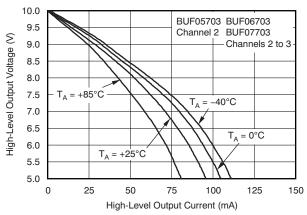


Figure 11.

#### HIGH-LEVEL OUTPUT VOLTAGE vs HIGH-LEVEL OUTPUT CURRENT

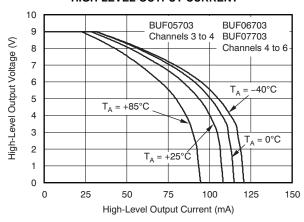


Figure 12.

#### HIGH-LEVEL OUTPUT VOLTAGE vs HIGH-LEVEL OUTPUT CURRENT

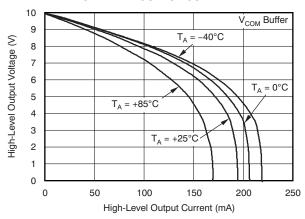


Figure 13.

#### LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT

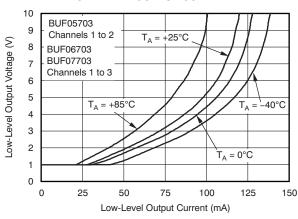


Figure 14.

#### LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT

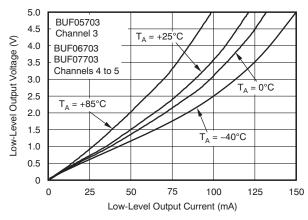


Figure 15.

#### LOW-LEVEL OUTPUT VOLTAGE vs LOW-LEVEL OUTPUT CURRENT

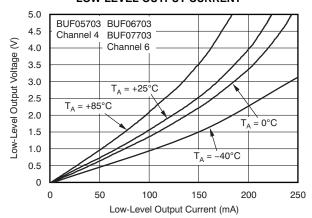


Figure 16.



At  $V_{DD}$  = 10V, unless otherwise noted.

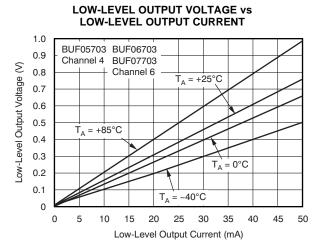
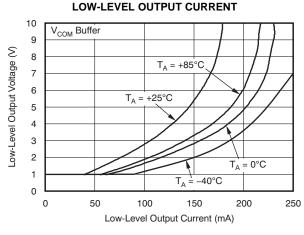


Figure 17.



**LOW-LEVEL OUTPUT VOLTAGE vs** 

Figure 18.

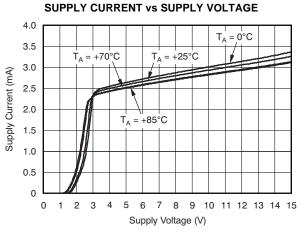


Figure 19.

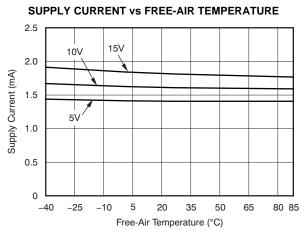


Figure 20.

## **AC CURVES**

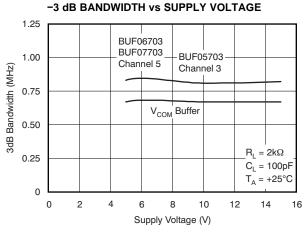


Figure 21.

#### POWER-SUPPLY REJECTION RATIO vs FREQUENCY

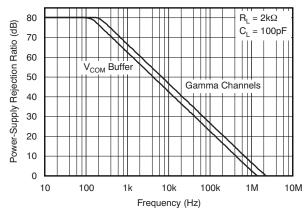


Figure 22.



At  $V_{DD}$  = 10V, unless otherwise noted.

## TRANSIENT CURVES

#### SUPPLY VOLTAGE, OUTPUT VOLTAGE, AND SUPPLY CURRENT

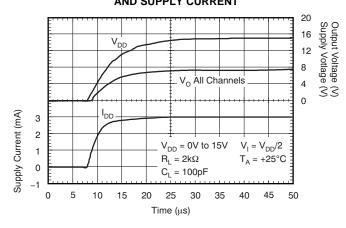


Figure 23.

#### LARGE-SIGNAL VOLTAGE FOLLOWER

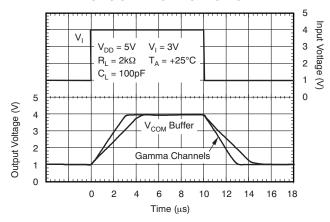


Figure 24.

#### LARGE-SIGNAL VOLTAGE FOLLOWER

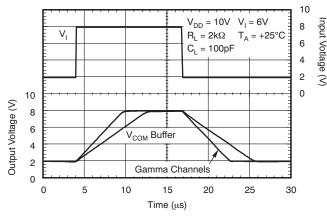


Figure 25.

#### LARGE-SIGNAL VOLTAGE FOLLOWER

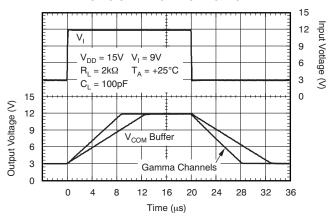


Figure 26.

#### **SMALL-SIGNAL VOLTAGE FOLLOWER**

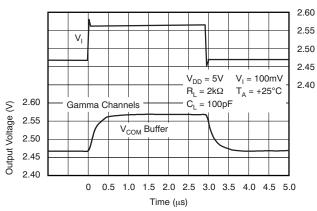


Figure 27.

#### **SMALL-SIGNAL VOLTAGE FOLLOWER**

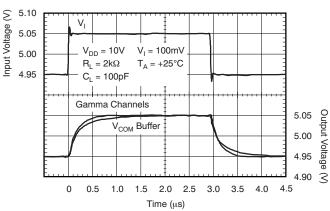


Figure 28.

Input Voltage

3



At  $V_{DD} = 10V$ , unless otherwise noted.

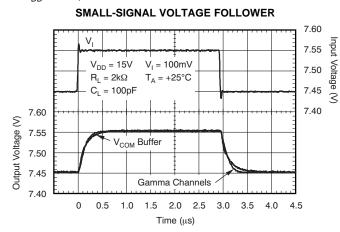


Figure 29.

#### TRANSIENT LOAD RESPONSE: SOURCING Input Voltage (V) 76543210 Transient Load Pulse Channel 1 $V_{DD} = 10V, V_I = 5V$ 5.15 $C_S$ = 100pF, $R_S$ = 100 $\Omega$ $C_L = 100 pF, R_L = 1 k\Omega$ 5.10 $= 0.1 \mu s$ , $T_{\Delta} = +25 ^{\circ} C$ Output Voltage (V) 5.05 5.00 4.95 4.90 **Output Voltage** 4.85 4.80 0.1 0.2 0.3 0.4 0.9 0.5 0.6 0.7 8.0 1.0

Time (μs)
Figure 30.

#### TRANSIENT LOAD RESPONSE: SINKING

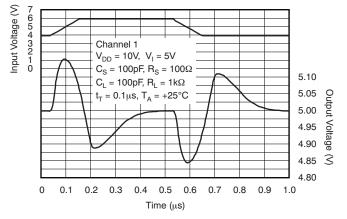


Figure 31.

#### TRANSIENT LOAD REGULATION: SINKING

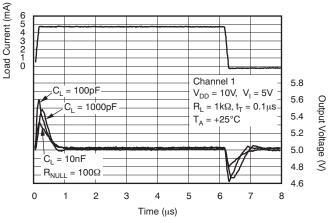


Figure 32.

#### TRANSIENT LOAD REGULATION: SOURCING

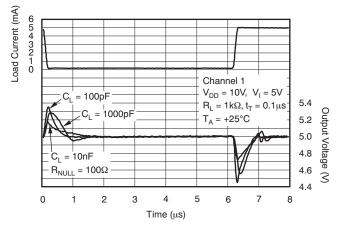


Figure 33.

## TRANSIENT LOAD REGULATION: V<sub>COM</sub> BUFFER

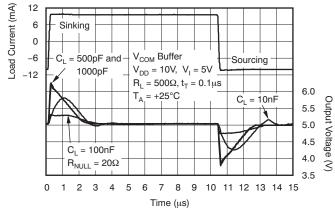


Figure 34.

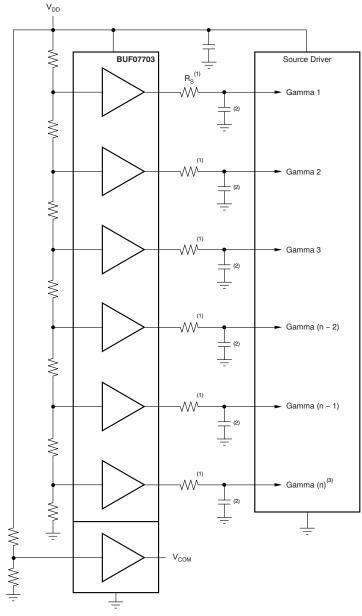


#### APPLICATION INFORMATION

The requirements on the number of gamma correction channels vary greatly from panel to panel. Therefore, the BUFxx703 series of gamma correction buffers offers different channel combinations. The  $V_{\text{COM}}$  channel can be used to drive the  $V_{\text{COM}}$  node on the LCD panel.

Gamma correction voltages are often generated using a simple resistor ladder, as shown in Figure 35.

The BUFxx703 buffers the various nodes on the gamma correction resistor ladder. The low output impedance of the BUFxx703 forces the external gamma correction voltage on the respective reference node of the LCD source driver. Figure 35 shows an example of the BUFxx703 in a typical block diagram driving an LCD source driver with 6-channel gamma correction reference inputs.



- (1) Optional; increases stability.
- (2) Stable without  $R_S$  up to  $30\mu F$ .
- (3) n = maximum number of gamma channels on respective BUFxx7703 devices.

Figure 35. LCD Source Driver Typical Block Diagram



#### **INPUT VOLTAGE RANGE GAMMA BUFFERS**

Figure 36 shows a typical gamma correction curve with 10 gamma correction reference points (GMA1 through GMA10). As can be seen from this curve, the voltage requirements for each buffer varies greatly. The swing capability of the input stages of the various buffers in the BUFxx703 is carefully matched to the application. Using the example of the BUF07703 with six gamma correction channels, buffers 1 to 3 have input stages that include  $V_{\rm DD}$ , but will only swing within 1V to GND. Buffers 1 through 5 have only a single NMOS input stage. Buffers 4 through 6 have only a single PMOS input stage. The input range of the PMOS input stage includes GND.

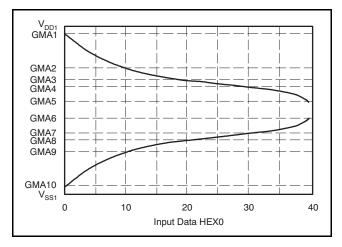


Figure 36. Gamma Correction Curve

# OUTPUT VOLTAGE SWING GAMMA BUFFERS

The output stages have been designed to match the characteristic of the input stage. Once again using the example of the BUF07703 means that the output stage of buffer 1 swings very close to V<sub>DD</sub>, typically V<sub>CC</sub> - 100mV at 5mA; its ability to swing to GND is limited. Buffers 2 and 3 have smaller output stages with slightly larger output resistances, as they will not have to swing as close to the positive rail as buffer 1. Buffers 4 through 6 swing closer to GND than V<sub>DD</sub>. Buffer 6 is designed to swing very close to GND, typically GND + 100mV at a 5mA load current. See the Typical Characteristics for more details. This approach significantly reduces the silicon area and cost of the whole solution. However, due to this architecture, the correct buffer needs to be connected to the correct gamma correction voltage.

Connect buffer 1 to the gamma voltage closest to  $V_{DD}$ , and buffers 2 and 3 to the sequential voltages. Buffer 6 should be connected to the gamma correction voltage closest to GND (or the negative rail), buffers 4 and 5 to the sequential higher voltages.

## COMMON BUFFER (V<sub>COM</sub>)

The common buffer output of the BUF07703 and BUF05703 has a greater output drive capability than the gamma correction buffers, to meet the heavier current demands of driving the common node of the LCD panel. It was also designed to drive heavier capacitive loads and still remain stable, as shown in Figure 37.

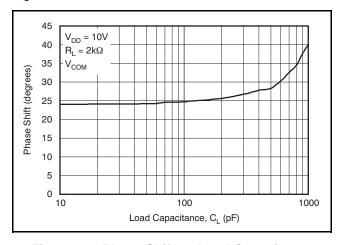


Figure 37. Phase Shift vs Load Capacitance

## **CAPACITIVE LOAD DRIVE**

The BUFxx703 has been designed to be able to sink/source DC currents in excess of 10mA. Its output stage has been designed to deliver output current transients with little disturbance of the output voltage. However, there are times when very fast current pulses are required. Therefore, in LCD source-driver buffer applications, it is quite normal for capacitors to be placed at the outputs of the reference buffers. These are to improve the transient load regulation. These will typically vary from 100pF and more. The BUFxx703 gamma buffers were designed to drive capacitances in excess of 100pF and retain effective phase margins above 50°, as shown in Figure 38.



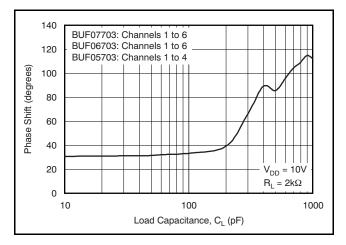


Figure 38. Phase Shift Between Output and Input vs Load Capacitance for the Gamma Buffers

# APPLICATIONS WITH >10 GAMMA CHANNELS

When a greater number of gamma correction channels are required, two or more BUFxx703 devices can be used in parallel, as shown in Figure 39. This provides a cost-effective way of creating more reference voltages over the use of quad-channel op amps or buffers. The suggested configuration in Figure 39 simplifies layout. The various different channel versions provide a high degree of flexibility and also minimize total cost and space. Table 1 lists a variety of gamma combinations for applications with more than 10 channels.

Table 1. > 10 Channel Gamma Combinations

	BUF11702	BUF07703	BUF06703	BUF05703
12ch	_	_	2	_
12ch + V <sub>COM</sub>	_	1	1	
14ch + V <sub>COM</sub>	1	_	_	1
16ch + V <sub>COM</sub>	1	_	1	_
18ch + V <sub>COM</sub>	2	_	_	_
20ch + V <sub>COM</sub>	2	_	_	_

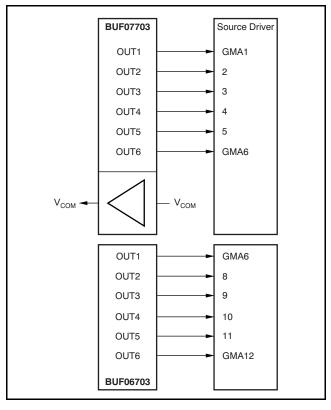


Figure 39. Creating > 10 Gamma Voltage Channels

## MULTIPLE V<sub>COM</sub> CHANNELS

In some LCD panels, more than one  $V_{COM}$  driver is required for best panel performance. Figure 40 uses three BUF07703s to create a total of 18 gamma-correction and three  $V_{COM}$  channels. This solution saves considerable space and cost over the more conventional approach of using five or six quad-channel buffers or op amps.



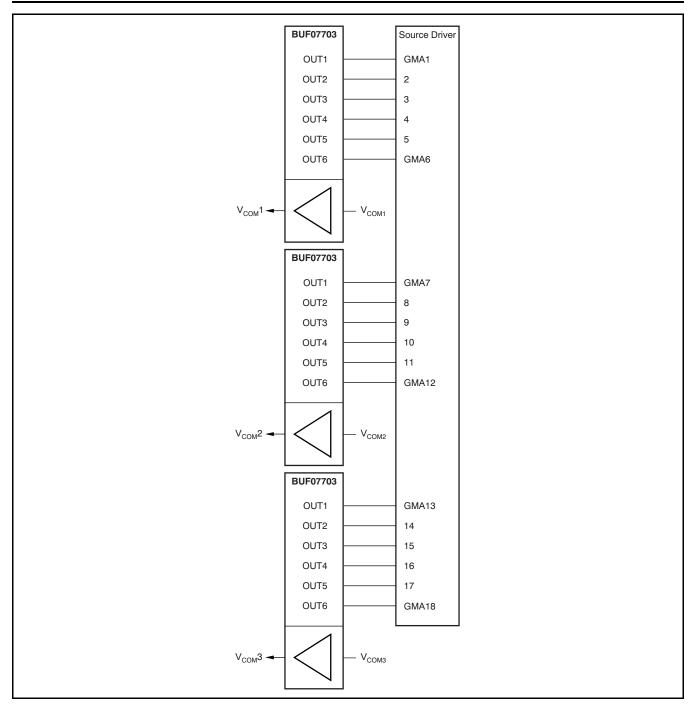


Figure 40. 18-Channel Application with Five Integrated V<sub>COM</sub> Channels

## **COMPLETE LCD SOLUTION FROM TI**

Besides the BUFxx703 line of gamma correction buffers, TI offers a complete set of ICs for the LCD panel market: source and gate drivers, various power-supply solutions, as well audio power solutions. Figure 41 shows the total IC solution from TI.

#### **Audio Power Amplifier for TV Speakers**

The TPA3002D2 is a 7W (per channel) stereo audio amplifier specifically targeted towards LCD monitors and TVs. It offers highly efficient, filter-free Class-D operation for driving bridged tied stereo speakers. The TPA3002D2 is designed to drive stereo speakers as low as  $8\Omega$  without an output filter. The high efficiency of the TPA3002D2 eliminates the need for external heatsinks when playing music. Stereo speaker volume is controlled with a dc voltage applied to the volume control terminal offering a range of gain from -40dB to +36dB. Line outputs, for driving external headphone amplifier inputs, are also dc voltage controlled with a range of gain from -56dB to +20dB. An integrated +5V regulated supply is provided for powering an external headphone

amplifier. Texas Instruments offers a full line of linear and switch-mode audio power amplifiers. For excellent audio performance TI recommends the OPA364 or OPA353 as headphone drivers. For more information visit www.ti.com.

# Integrated DC/DC Converter for LCD Panels: TPS65100

The TPS65100 offers a very compact and small power supply solution to provide all three power-supply voltages required by TFT (thin film transistor) LCD displays. Additionally the device has an integrated V<sub>COM</sub> buffer. The auxiliary linear regulator controller can be used to generate the 3.3V logic power rail for systems powered by a 5V supply rail only. The main output can power the LCD source drivers as well as the BUFxx703. An integrated adjustable charge pump doubler/tripler provides the positive LCD gate drive voltage. An externally adjustable negative charge pump provides the negative gate drive voltage. The TPS65100 has an integrated V<sub>COM</sub> buffer to power the LCD backplane. A version of the BUFxx703 without the integrated V<sub>COM</sub> buffer could be used for minimum redundancy and lowest cost. For LCD panels powered by 5V only, the TPS65100 has a linear regulator controller that uses an external transistor to provide a regulated 3.3V output for the digital circuits. Contact the local sales office for more information.

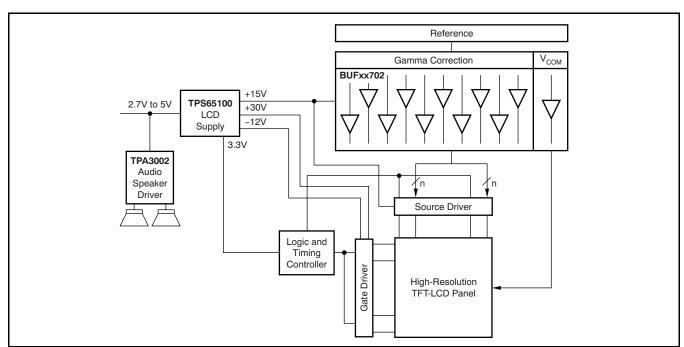


Figure 41. TI LCD Solution



# GENERAL PowerPAD DESIGN CONSIDERATIONS

The BUF07703 is available in the thermally enhanced PowerPAD family of packages. These packages are constructed using a downset leadframe upon which the die is mounted; see Figure 42(a) and (b). This arrangement results in the lead frame being exposed as a thermal pad on the underside of the package; see Figure 42(c). Due to this thermal pad having direct thermal contact with the die, excellent thermal performance is achieved by providing a good thermal path away from the thermal pad.

The PowerPAD package allows for both assembly and thermal management in one manufacturing operation. During the surface-mount solder operation (when the leads are being soldered), the thermal pad can also be soldered to a copper area underneath the package. Through the use of thermal paths within this copper area, heat can be conducted away from the package into either a ground plane or other heat-dissipating device. Although there are many ways to properly heatsink the PowerPAD package, the following steps illustrate the recommended approach.

- 1. Prepare the PCB with a top-side etch pattern, (see Pin Configurations). There must be etching for the leads as well as etch for the thermal pad.
- Place 18 holes in the area of the thermal pad. These holes must be 13 mils in diameter. Keep them small, so that solder wicking through the holes is not a problem during reflow.
- 3. Additional vias may be placed anywhere along the thermal plane outside of the thermal pad area. This helps dissipate the heat generated by the BUF07703 IC. These additional vias may be larger than the 13-mil diameter vias directly under the thermal pad. They can be larger because they are not in the thermal pad area to be soldered, so that wicking is not a problem.
- 4. Connect all holes to the internal ground plane.
- 5. When connecting these holes to the ground plane, do not use the typical web or spoke via connection methodology. Web connections have a high thermal resistance connection that is useful for slowing the heat transfer during

- soldering operations. This makes the soldering of vias that have plane connections easier. In this application, however, low thermal resistance is desired for the most efficient heat transfer. Therefore, the holes under the BUF07703 PowerPAD package must make their connection to the internal ground plane with a complete connection around the entire circumference of the plated-through hole.
- 6. The top-side solder mask must leave the terminals of the package and the thermal pad area with its five holes (dual) or nine holes (quad) exposed. The bottom-side solder mask must cover the five or nine holes of the thermal pad area. This prevents solder from being pulled away from the thermal pad area during the reflow process.
- Apply solder paste to the exposed thermal pad area and all of the IC terminals.
- 8. With these preparatory steps in place, the BUF07703 IC is simply placed in position and run through the solder reflow operation as any standard surface-mount component. This results in a part that is properly installed.

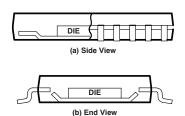
For a given  $\theta_{JA}$ , the maximum power dissipation is calculated by the following formula:

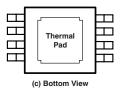
$$P_{D} = \left(\frac{T_{MAX} - T_{A}}{\theta_{JA}}\right)$$

#### Where:

- P<sub>D</sub> = maximum power dissipation (W)
- T<sub>MAX</sub> = absolute maximum junction temperature (+150°C)
- T<sub>A</sub> = free-ambient air temperature (°C)
- $\theta_{JA} = \theta_{JC} + \theta_{CA}$
- θ<sub>JC</sub> = thermal coefficient from junction to case (°C/W)
- $\theta_{CA}$  = thermal coefficient from case-to-ambient air (°C/W)

This lower thermal resistance enables the BUF07703 to deliver maximum output currents even at high ambient temperatures.





Note: The thermal pad is electrically isolated from all terminals in the package.

Figure 42. Views of Thermally-Enhanced DGN Package



## **REVISION HISTORY**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	nanges from Revision B (November, 2007) to Revision C	Page
•	Updated document format to current standards	1
•	Updated Features bullet: changed temperature specification lower limit from 0°C to -40°C	1
•	Updated format of Package Information table	2
•	Deleted lead temperature specification from, changed operating free-air temperature specification in <i>Absolute Maximum Ratings</i>	2
•	Changed operating free-air temperature specification in Recommended Operating Conditions to -40°C	2
•	Changed footnote to Electrical Characteristics table	3
•	Changed footnote to Electrical Characteristics: BUF07703 table	4
•	Changed footnote to Electrical Characteristics: BUF07703 table	5
•	Changed footnote to Electrical Characteristics: BUF07703 table	6
•	Updated Typical CharacteristicsFigure 9 through Figure 18	9
•	Replaced Figure 20	11
•	Deleted previous Figure 21 (-3dB Bandwidth vs Free-Air Temperature graph)	11





21-Mar-2013

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing		Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
BUF05703PW	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI	-40 to 85	BUF05703	
BUF05703PWG4	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI	-40 to 85		
BUF05703PWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	BUF05703	Samples
BUF05703PWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	BUF05703	Samples
BUF06703PW	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	-40 to 85		
BUF06703PWG4	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	-40 to 85		
BUF06703PWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	BF06703	Samples
BUF06703PWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	BF06703	Samples
BUF07703PWP	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BUF07703	Samples
BUF07703PWPG4	ACTIVE	HTSSOP	PWP	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BUF07703	Samples
BUF07703PWPR	OBSOLETE	HTSSOP	PWP	20		TBD	Call TI	Call TI	-40 to 85	BUF07703	
BUF07703PWPRG4	OBSOLETE	HTSSOP	PWP	20		TBD	Call TI	Call TI	-40 to 85	BUF07703	

<sup>&</sup>lt;sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): Tl's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, Tl Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



## **PACKAGE OPTION ADDENDUM**

21-Mar-2013

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Only one of markings shown within the brackets will appear on the physical device.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

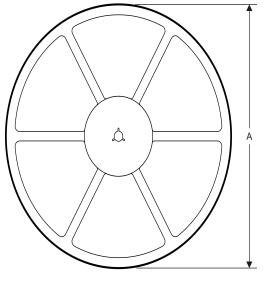
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

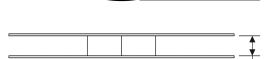
## PACKAGE MATERIALS INFORMATION

www.ti.com 17-Aug-2012

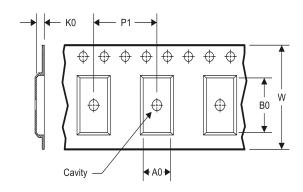
## TAPE AND REEL INFORMATION

## **REEL DIMENSIONS**





## TAPE DIMENSIONS



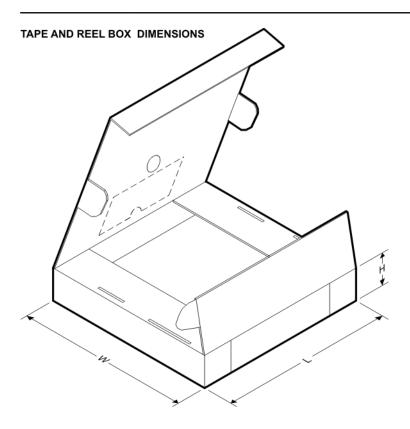
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## TAPE AND REEL INFORMATION

\*All dimensions are nominal

All differsions are nonlinal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BUF05703PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
BUF06703PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
BUF06703PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

www.ti.com 17-Aug-2012

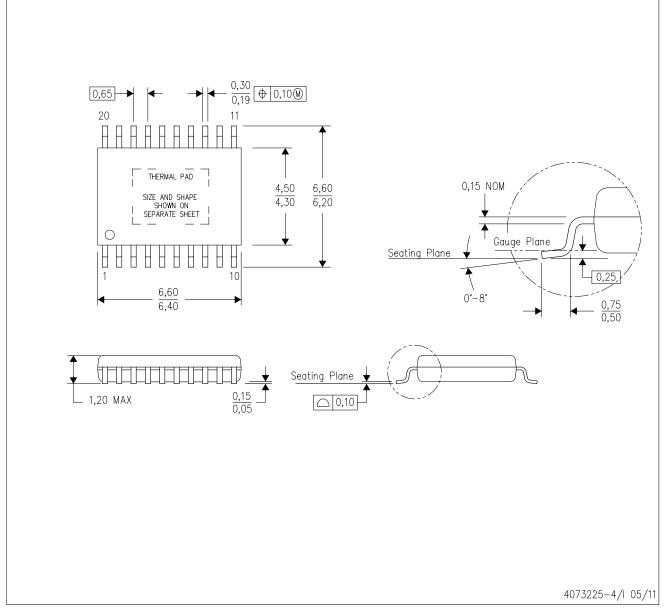


#### \*All dimensions are nominal

7 III GITTIOTIOTOTIO GITO TIOTITITICA							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BUF05703PWR	TSSOP	PW	14	2000	367.0	367.0	35.0
BUF06703PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
BUF06703PWR	TSSOP	PW	16	2000	367.0	367.0	35.0

PWP (R-PDSO-G20)

## PowerPAD ™ PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
- This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="http://www.ti.com">http://www.ti.com</a>.

  E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- E. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.



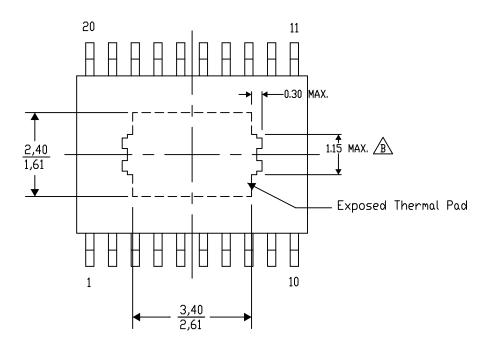
# PWP (R-PDSO-G20) PowerPAD™ SMALL PLASTIC OUTLINE

#### THERMAL INFORMATION

This PowerPAD<sup>TM</sup> package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Top View

Exposed Thermal Pad Dimensions

4206332-15/AD 01/13

NOTE: A. All linear dimensions are in millimeters

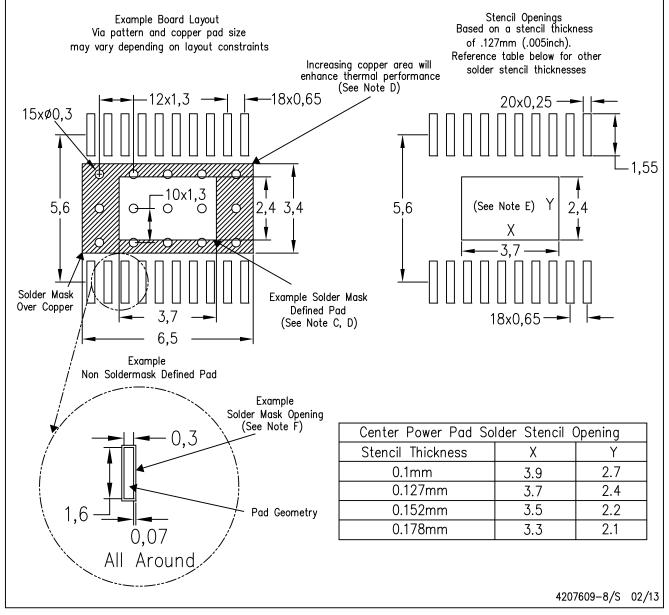
Exposed tie strap features may not be present.

PowerPAD is a trademark of Texas Instruments



## PWP (R-PDSO-G20)

## PowerPAD™ PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="https://www.ti.com">http://www.ti.com</a>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

## PLASTIC SMALL OUTLINE

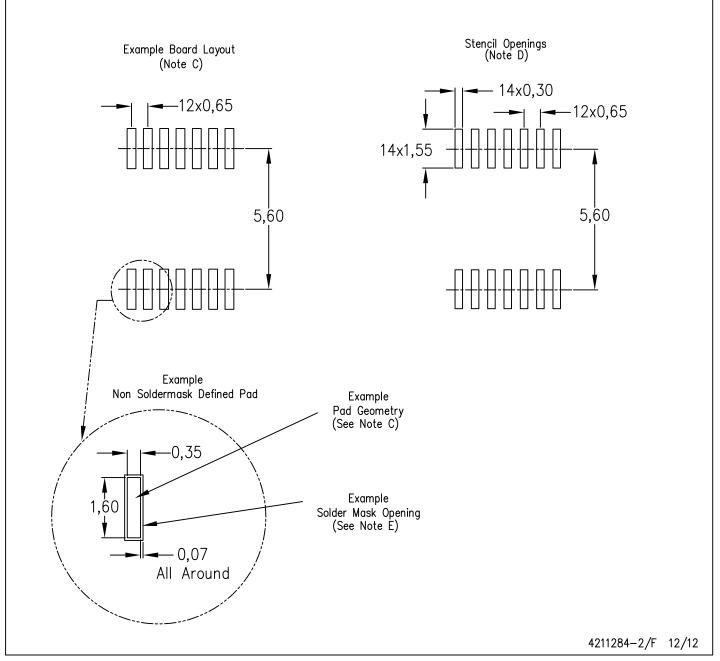


- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



# PW (R-PDSO-G14)

## PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G16)

## PLASTIC SMALL OUTLINE

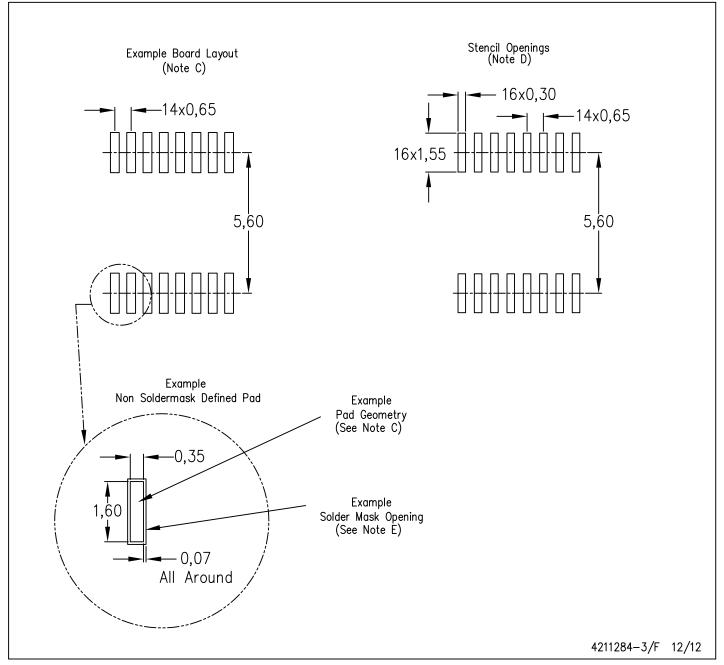


- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



# PW (R-PDSO-G16)

## PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



#### IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products Applications

Audio www.ti.com/audio Automotive and Transportation www.ti.com/automotive Communications and Telecom **Amplifiers** amplifier.ti.com www.ti.com/communications **Data Converters** dataconverter.ti.com Computers and Peripherals www.ti.com/computers **DLP® Products** www.dlp.com Consumer Electronics www.ti.com/consumer-apps

DSP **Energy and Lighting** dsp.ti.com www.ti.com/energy Clocks and Timers www.ti.com/clocks Industrial www.ti.com/industrial Interface interface.ti.com Medical www.ti.com/medical logic.ti.com Logic Security www.ti.com/security

Power Mgmt power.ti.com Space, Avionics and Defense www.ti.com/space-avionics-defense

Microcontrollers <u>microcontroller.ti.com</u> Video and Imaging <u>www.ti.com/video</u>

RFID www.ti-rfid.com

OMAP Applications Processors <u>www.ti.com/omap</u> TI E2E Community <u>e2e.ti.com</u>

Wireless Connectivity <u>www.ti.com/wirelessconnectivity</u>



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

## Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов:
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001:
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина,

дом 2, корпус 4, литера А.